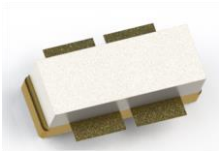
XTAH50120F4C GaN TRANSISTC

Document Number: XTAH50120F4C
Preliminary Datasheet V1.0

GaN 28V 120W, C band RF Power Transistor

XTAH50120F4C



Description

The XTAH50120F4C is a 120W internally matched, GaN HEMT, designed from 4.4 to 5.0GHz, especially 5G NR or LTE application, as well as either Pulse or CW application There is no guarantee of performance when this part is used in applications designed Outside of these frequencies.

- Typical **CW** performance (on 4.4-5.0GHz fixture with device soldered)：

Vds=28V, I_{DQ}=150mA

Freq (MHz)	P1dB (dBm)	P1dB (W)	P1dB Eff(%)	P1dB Gain(dB)	P3dB (dBm)	P3dB (W)	P3dB Eff(%)
4300	50.48	111.6	50.2	11.33	51.37	137.0	51.8
4400	50.52	112.7	51.0	11.42	51.41	138.4	52.7
4500	50.52	112.7	51.7	11.62	51.43	138.9	53.4
4600	50.51	112.5	51.9	12.11	51.44	139.4	53.6
4700	50.39	109.3	52.2	12.32	51.36	136.9	53.8
4800	49.98	99.5	51.2	12.15	51.09	128.6	53.0
4900	49.81	95.8	51.1	11.71	51.02	126.4	53.6
5000	49.61	91.4	51.4	11.16	50.87	122.2	54.3
5100	49.05	80.3	50.6	11.08	50.45	110.9	54.3

Recommended driver：GTAH35025P3

Applications and Features

- Suitable for wireless communication infrastructure, wideband amplifier, EMC testing, ISM etc.
- High Efficiency and Linear Gain Operations
- Thermally Enhanced Industry Standard Package
- High Reliability Metallization Process
- Excellent thermal Stability and Excellent Ruggedness
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Important Note: Proper Biasing Sequence for GaN HEMT Transistors

Turning the device ON

1. Set VGS to the pinch--off (VP) voltage, typically –5 V
2. Turn on VDS to nominal supply voltage (28V)
3. Increase VGS until IDS current is attained
4. Apply RF input power to desired level

Turning the device OFF

1. Turn RF power off
2. Reduce VGS down to VP, typically –5 V
3. Reduce VDS down to 0 V
4. Turn off VGS

Figure 1: Pin definitions (Top view)

Because of internal configuration, it must be used as single ended device.

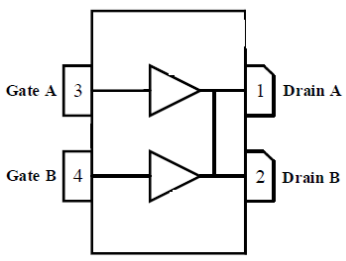


Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	150	Vdc
Gate--Source Voltage	V_{GS}	-10,+2	Vdc
Operating Voltage	V_{DD}	36	Vdc
Maximum Forward Gate Current @ TC = 25°C	Igmax	33.6	mA
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	T_C	+150	°C
Operating Junction Temperature(See note 1)	T_J	+225	°C
Total Device Power Dissipation (Derated above 25°C, see note 2)	Pdiss	150	W

Note: 1. Continuous operation at maximum junction temperature will affect MTTF
2.Bias Conditions should also satisfy the following expression: Pdiss < (Tj – Tc) / RJC and Tc = Tcase

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case T_C= 85°C, T_J=200°C, RF CW operation	RθJC	0.85	C/W

Table 3. Electrical Characteristics (T_C = 25℃ unless otherwise noted)

DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{GS}=-8V; I_{DS}=33.6mA	V_{DSS}	150			V
Gate Threshold Voltage	V_{DS} = 28V, I_D =33.6mA	V_{GS}(th)	-4		-2	V
Gate Quiescent Voltage	V_{DS} =28V, I_{DS}=500mA, Measured in Functional Test	$V_{GS(Q)}$		-2.5		V

Typical performance

Figure 2: Small singal gain and return loss Vs Frequency
Vds=28V, Idq=500mA, input power=0dBm

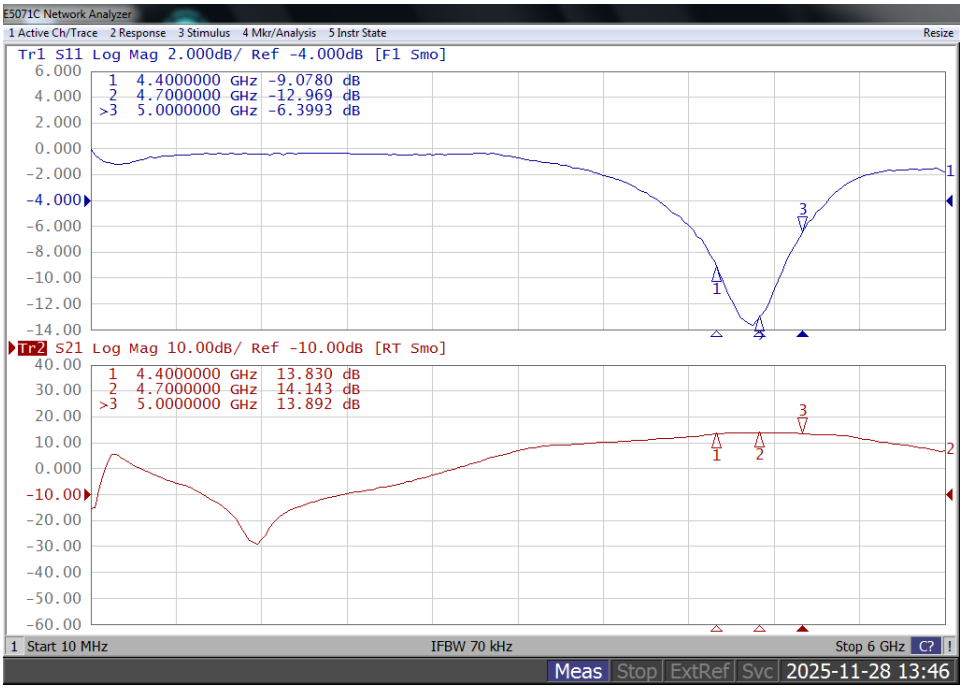
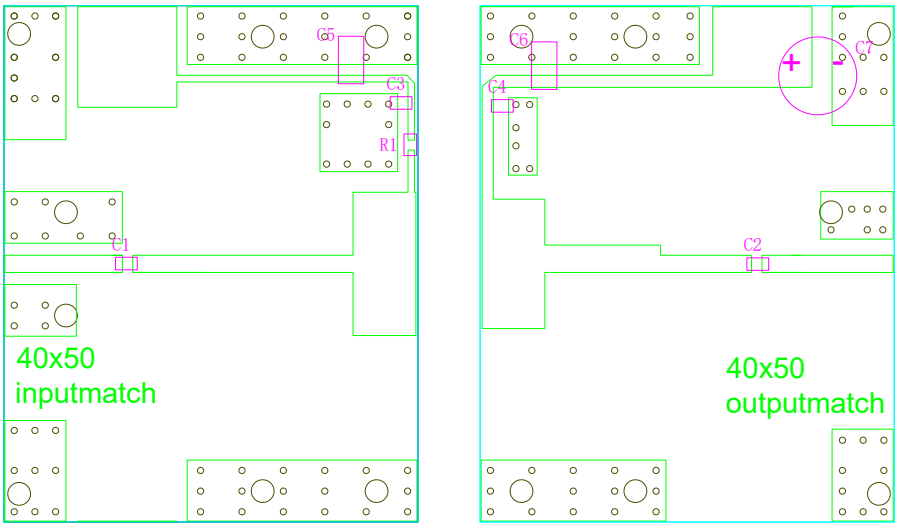
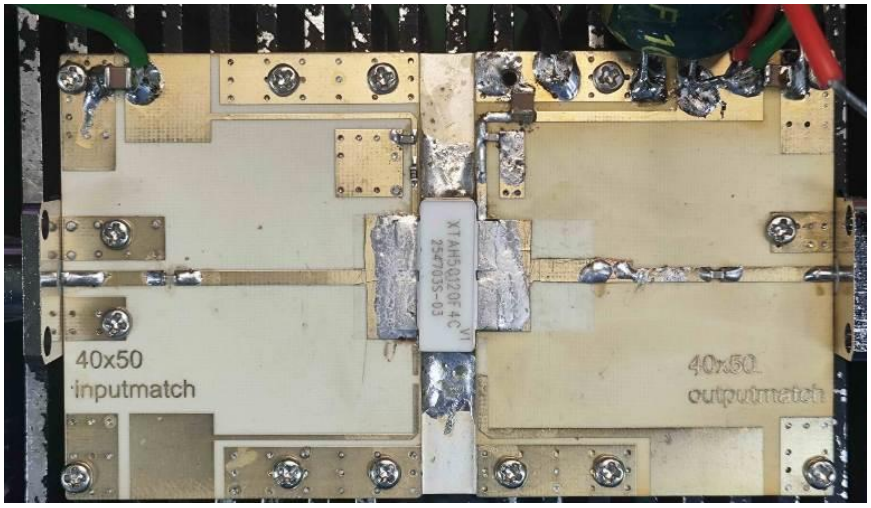


Figure 3: Picture and Bill of materials of wide band application circuit

(Layout Gerber file upon request)

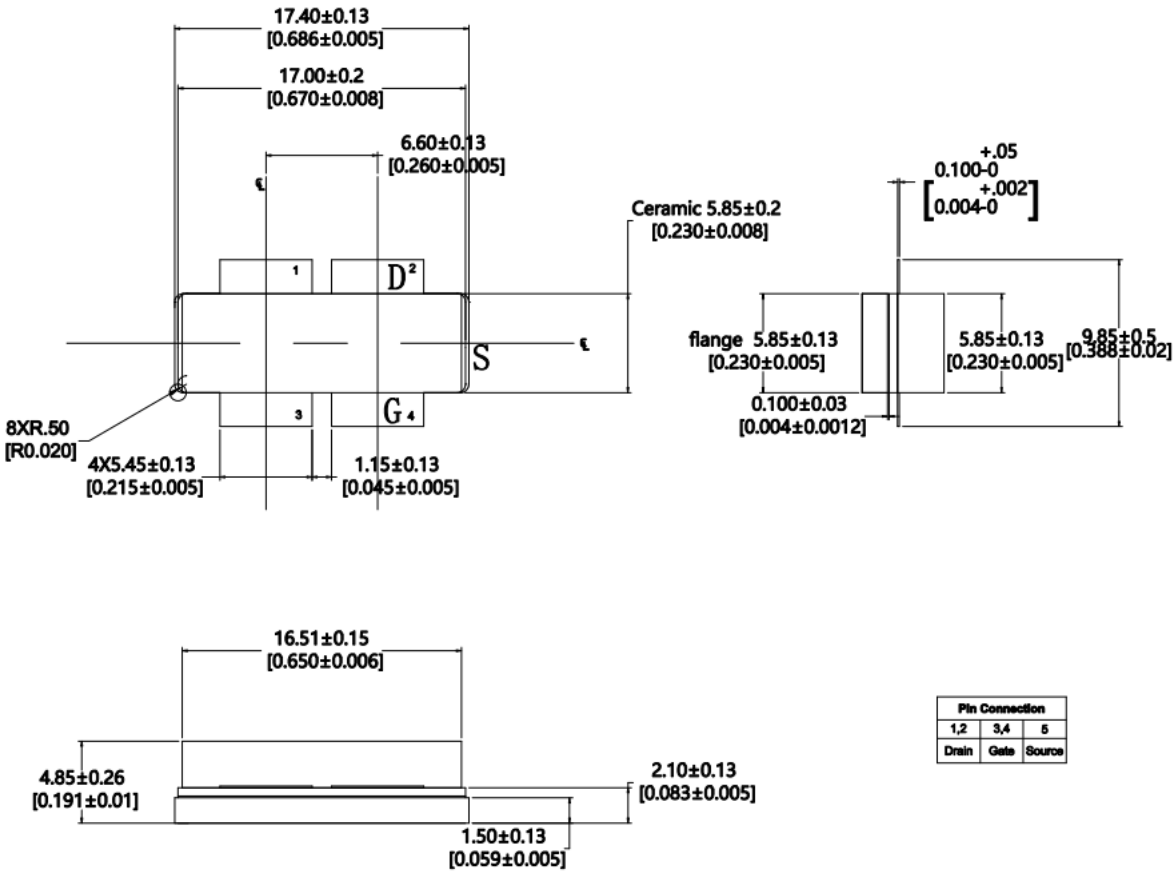




Designator	Comment	Footprint	Quantity
C1, C2, C3, C4	3.9 pF/250V	0805	1
C5, C6	10uF/100V	1210	2
C7	1000uF/63V		1
R1	10 Ω	0603	1

Package Outline

Flangeless ceramic package; 4 leads



OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-LBS					07/31/2023

Revision history

Table 4. Document revision history

Date	Revision	Datasheet Status
2025/11/28	V1.0	Preliminary Datasheet Creation

Application data based on LSM-25=36